

Silicon NPN Power Transistors

2SD1455

DESCRIPTION

- With TO-3PN package
- High voltage,high speed
- Built-in damper diode

APPLICATIONS

- For TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

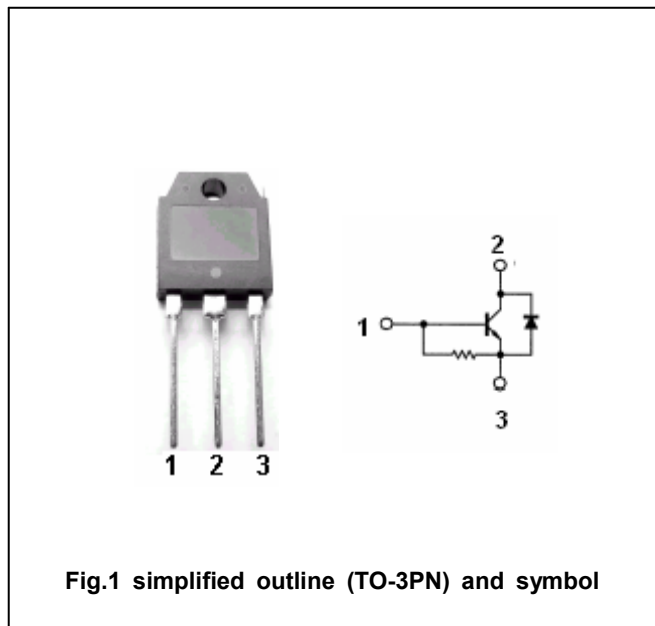


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current (DC)		5	A
P _C	Collector power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-45~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =200mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A; I _B =1.2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A; I _B =1.2A			1.5	V
I _{CB0}	Collector cut-off current	V _{CB} =1500V; I _E =0			0.5	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	6			
V _F	Diode forward voltage	I _F =5A			2.2	V

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PACKAGE OUTLINE

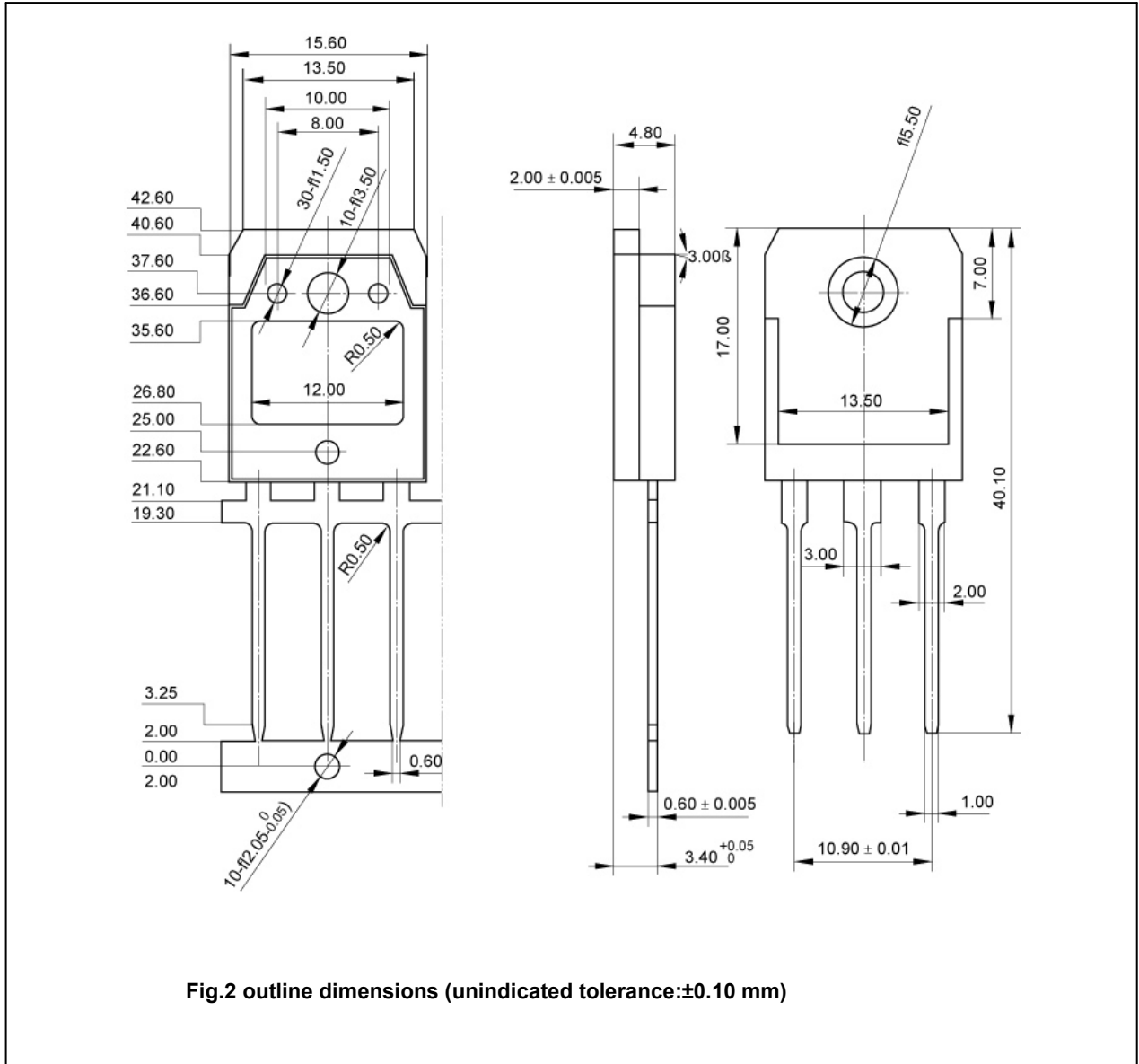


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)